		4 Marks: 60
	(Note: Assume suitable data if necessary) PART-A	
	Answer all TEN questions (Compulsory)	0x1=10M
1. S	olve $(3x^2 + 6xy^2)dx + (6x^2y + 4y^3)dy = 0$.	1 M
	tate law of natural growth.	1 M
	olve $y'' - 2y' + 10y = 0$.	1 M
4. Fi	ind the P. I. of $(D^2 + 2D + 1)y = e^{-x}$.	1 M
5. C	ompute the Laplace transform of $(\sin t - \cos t)^2$.	1 M
6. Fi	ind the inverse Laplace transform of $\frac{1}{s^2 - 5s + 6}$.	1 M
	ind a unit vector normal to the surface $x^3 + y^3 + 3xyz = 3$ at the point $(1, 2, -1)$.	1 M
	$\mathbf{F} = (x + y + 1) \mathbf{i} + \mathbf{j} - (x + y) \mathbf{k}$, show that \mathbf{F} . curl $\mathbf{F} = 0$. valuate div \mathbf{F} at the point $(1, 2, 3)$ where $\mathbf{F} = x^2yz \mathbf{i} + xy^2z \mathbf{j} + xyz^2 \mathbf{k}$.	1 M 1 M
(3	alculate the angle between the normal to the surface $xy = z^2$ at the points (4, 1, 2), 3, -3). PART-B swer the following. Each question carries TEN Marks.	and 1 M
11.A).	Solve $\cosh x \frac{dy}{dx} + y \sinh x = 2 \cosh^2 x \sinh x$.	10M
	OR	
	If the temperature of the air is 30°C and the substance cools from 100°C to 70°C in	
11. B).	minutes, find when the temperature will 40°C.	n 15 10M
,		10M 10M
,	minutes, find when the temperature will 40°C.	
,	minutes, find when the temperature will 40°C. Solve $(D^3 + 2D^2 + D)y = x^2e^{2x} + \sin^2 x$.	
12. A).	minutes, find when the temperature will 40°C. Solve $(D^3 + 2D^2 + D)y = x^2e^{2x} + \sin^2 x$. OR	10M
12. A). 12. B). 13. A).	minutes, find when the temperature will 40°C. Solve $(D^3 + 2D^2 + D)y = x^2e^{2x} + \sin^2 x$. OR Solve by the method of variation of parameters: $y'' + y = \sec x$. Apply Convolution theorem to evaluate $L^{-1}\left[\frac{s}{\left(s^2 + 9\right)^2}\right]$. OR	10M 10M 10M
12. A). 12. B).	minutes, find when the temperature will 40°C. Solve $(D^3 + 2D^2 + D)y = x^2e^{2x} + \sin^2 x$. OR Solve by the method of variation of parameters: $y'' + y = \sec x$. Apply Convolution theorem to evaluate $L^{-1}\left[\frac{s}{\left(s^2 + 9\right)^2}\right]$.	10M 10M

14. A). Find the values of constants a, b, c so that the directional derivative of 10M $p = axy^2 + byz + cz^2x^3$ at (1, 2, -1) has a maximum magnitude 64 in the direction parallel to the z-axis.

OR

14. B). If $f = (x^2 + y^2 + z^2)^{-n}$, find div grad f and determine n if div grad f = 0.

15. A). Verity Stoke's theorem for $\mathbf{F} = (y - z + 2) \mathbf{i} + (yz + 4) \mathbf{j} - xz \mathbf{k}$ where S is the surface of the cube x = 0, y = 0, z = 0, x = 2, y = 2, z = 2 above the xy-plane.

OR

15. B). Verify Green's theorem for $\int_C \left[\left(3x - 8y^2 \right) dx + \left(4y - 6xy \right) dy \right]$ where C is the boundary of the region bounded by x = 0, y = 0 and x + y = 1.



C	B.Tech II Semester Regular/Supplementary Examinations July/Au ourse Name: Engineering Chemistry	gust-2024	
	(Common for CE, ME, CSC, CSM, CSD & AIM)		
Da	ate: 18.07.2024 FN Time: 3 hours	Max.Marks: 6	60
	(Note: Assume suitable data if necessary) PART-A		
	Answer all TEN questions (Compulsory) Each question carries ONE mark.	10x1=10N	M
1. D	Define standard oxidation potential and standard reduction method.	1	I M
2. C	Compare primary and secondary batteries (any two).	1	l M
3. V	What is condensation polymerization. Give an example.	. 1	l M
4. D	Define biodegradable polymers.	- 1	M
5. W	What is cetane number of a diesel fuel.	1	M
6. M	fention the composition of LPG.	1	M
7. D	befine hardness. What are its units.	1	M
8. G	ive the ions causing permanent hardness in water.	1	M
9. L	ist out any four general properties of glass.	1	M
10. W	hat is meant by flash point of a lubricant.	1	M
	DADE D		
An	PART-B aswer the following. Each question carries TEN Marks.	5x10=50I	M
11.A).	i) Explain electrochemical series and mention its applications.		4M
	ii) Explain the construction and the various reactions involved in disc charging in a lead acid storage battery.		6M
	OR		
11. B).	i) Define corrosion and list out the factors affecting corrosion in detail.		5M
	ii) With a neat, labelled diagram explain galvanic and waterline corrosion.		5M
12. A).	i) Give the preparation, properties and applications of polyvinyl chloride.ii) What are plastics? Write short notes on compression moulding with diagram.		4M 6M
	OR		
12. B).	i) Write short notes on fibre reinforced plastics (FRP). What are its application ii) Explain the mechanism of conduction in trans polyacetylene and also applications.		4M 6M
13. A).	i) Write short notes on ultimate analysis of coal and give its significance. ii) Calculate the gross and net calorific value of coal having the following coarbon = 83%, Hydrogen = 8%, Sulphur = 3%, Nitrogen = 2%, Ash = 4%, I steam = 587 cal/g.	ompositions:	5M 5M
		(P, T, O)	

13. B).	1) Explain Fischer-Tropsch method for synthesis of petrol.	5M
	ii) Explain catalytical cracking of petrol by moving bed catalytic method.	5M
14. A).	by the amount of the modern process. With a float label diagram.	5M
2),	ii) Calculate the quantity of lime and soda required for softening of 50,000 litres of water containing the following impurities: Ca(HCO3)2 =9.2mg/L, Mg(HCO3)2 = 7.9 mg/L, CaSO4 = 15.3 mg/L, MgSO4 = 15.0 mg/L, MgCl2 = 3.0 mg/L, NaCl = 4.0 mg/L.	5M
	OR	
14. B).	i) What is the principle involved in reverse osmosis. Mention its advantages.	5M
	ii) A sample of hard water contains the following dissolved salts per litre. CaCl2 = 111mgs, CaSO4 = 1.36mgs, Ca(HCO3)2 = 16.2mgs, Mg(HCO3)2 = 14.6mgs, silica = 40mgs, turbidity = 10mgs. Calculate the temporary, permanent and total hardness of water in ppm, degree Clarke and degree French.	5M
15. A).	i) Discuss extreme pressure lubrication and additives to improve the lubricant properties.	5M
	ii) Write short notes on smart materials. What are its applications?	5M
	OR	
15. B).	i) Explain setting and hardening of portland cement.	6M
	ii) Write short notes on strength of glass and glass articles.	4M



Co	B.Tech II Sen urse Name: Applie	(UGC AUTONOMOUS) nester Regular/Supplementary Examinations July/August-2024	
	e: 18.07.2024 FN	(Common for EEE, ECE, CSE & IT) Time: 3 hours Max.Mark	s: 60
	0	(Note: Assume suitable data if necessary) PART-A Answer all TEN questions (Compulsory) Each question carries ONE mark. 10x1=1	10M
1. M	ention any two proper	ties of matter waves.	1 M
2. De	efine Fermi energy.		1 N
3. M	ention any two differe	ences between the P-N junction and Zener diode.	1 N
4. W	rite any four application	ons of solar cells.	1 N
5. Ex	plain the characteristi	cs of LASER compared to ordinary light.	1 M
6. Ex	plain the principle inv	volved in the optical fiber.	1 M
	•	oelectricity ii. pyroelectricity	1 N
	•	between Hard and Soft magnetic materials	1 N
	• • • • • • • • • • • • • • • • • • • •	ons of energy materials	1 M
10. W	hat is the significance	of the surface-to-volume ratio of nanostructures?	1 N
An	ower the following F	PART-B ach question carries TEN Marks. 5x10=	:50M
All	wer the following. E	acti question carries 1214 Marks.	30111
11.A).	it enabled the verific	vaves? Describe Davisson and Germer's experiment and explain how ation of the wave nature of matter.	8N
	ii) Find the waveleng	gth of an electron if it is accelerating by potential 100V. OR	2N
11. B).	, <u>*</u>	features and drawbacks of classical free electron theory.	4N 6N
	help of energy level		
12. A).	_	of the Hall effect and discuss its importance in measuring the nature d carrier concentration.	10N
		OR	
12. B).	Explain the principle	e, construction and working of LED with a neat diagram.	. 10N
13. A).	i) Explain the sponta	neous and stimulated emissions.	3N
,		struction of the Ruby laser and discuss its working with the relevant	7N
		OR	
13. B).	i) Derive the express	ions for acceptance angle and numerical aperture.	8N
13. 15).			77
13. D).	ii) Draw the block di	agram of the fiber optic communication system. (P.T.O)	2N

14. A).	Explain various polarization mechanisms in dielectrics.	10M
	OR	
14. B).	i) Draw and explain the B-H curve for a ferromagnetic material based on domain theory.	7M
	ii) Discuss any two magnetic sensors and applications.	3M
15. A).	Explain the importance of supercapacitors. Discuss the role of different materials and electrolytes for supercapacitors.	10M
	OR	
15. B).	i) Write a short note on the importance of Sol-gel synthesis methods to prepare nanostructures.	7M
	ii) Explain the characterization technique by XRD.	3M



	ourse Name: Engine te: 20.07.2024 FN	(Common for CE & ME) Time: 3 hours Max.Marl	ks: 60
		(Note: Assume suitable data if necessary)	
		PART-A Answer all TEN questions (Compulsory) Each question carries ONE mark. 10x1=	:10M
. D	efine conic sections.		1 N
. C	lassify different types o	f scales.	1 M
3. O	utline the conditions of	third angle of projection.	1 M
. Po	oint A is 30 mm above	HP and 45 mm in front of VP. Draw its front view and top view.	1 N
. C	lassify different types o	f solids.	1 M
5. W	hat is solid of revolution	on?	1 N
. W	hat is a cycloid?		1 N
. Li	ist out different method	s of development of surfaces.	1 N
). D	efine Isometric scale.		1 N
0. W	hat is meant by project	ors?	1 N
		PART-B	
An	swer the following. Ea		=50M
1.A).	•		10N
		OR	
1. B).	A circle of 40 mm d point R on the circum	liameter rolls on a horizontal line. Draw the curve traced out by a ference of the circle.	10N
2. A).		g has its end P in both HP and VP. It is inclined at an angle of 30° to raw the projections of the line.	10N
		OR	
.2. B).		of a regular hexagonal lamina of 25 mm side, resting on HP on one ane perpendicular to HP and inclined at 45° to VP. Take the nearest way from VP.	10N
3. A).		of cylinder, base 30 mm diameter and axis 40 mm long, resting with cle on HP such that the axis is making an angle of 30° with HP and	10N
		OR	
3. B).		of base 25 mm and axis 50 mm long, rests with one of its edges on a containing that edge makes an angle of 30° to HP and its axis is its projections.	10M

14. A). A square pyramid of base 30 mm and axis 60 mm long is standing on HP with its base edges equally inclined to VP. It is cut by a section plane perpendicular to VP and inclined at 30° to HP through bisecting the axis. Draw the sectional top view and the true shape of the section, if the upper portion is removed.

OR

- 14. B). A hexagonal prism, edge of base 20 mm and axis 50 mm long, rests with its base on HP such that one of its rectangular faces is parallel to VP. It is cut by a plane perpendicular to VP, inclined at 45° to HP and passing through the right corner of the top face of the prism. (i) Draw the sectional top view. (ii) Develop the lateral surfaces of the truncated prism.
- 15. A). A cone of base diameter 50 mm and axis height 65 mm is resting on 50mm side of cube which its another side parallel to VP. Draw its isometric projection.

OR

15. B). Convert the pictorial view of an object shown in figure-1, to multiple views (Front, top and Side view) and mark the dimensions.

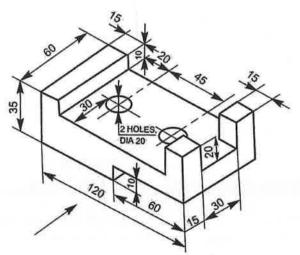


Figure -1 (All the dimensions are in mm)



	B.Tech II Semester Regular/Supplementary Examinations July/August-2024 Course Name: Analog Electronics Circuits	
	(Electrical & Electronics Engineering) Date: 20.07.2024 FN Time: 3 hours Max.Marks	s: 60
	(Note: Assume suitable data if necessary) PART-A Answer all TEN questions (Compulsory) Each question carries ONE mark. 10x1=1	0M
1.	Draw the V-I characteristics of a pn junction diode.	1 M
2.	Define ripple factor and efficiency of half wave rectifier.	1 M
3.	Compare JFET and MOSFET.	1 M
4.	Draw the small signal equivalent circuit of JFET at high frequency.	1 M
5.	Mention the different configurations of differential amplifiers.	1 M
6.	What are the advantages and disadvantages of class B power amplifier?	1 M
7.	What is the effect of negative feedback on amplifier characteristics?	1 M
8.	State Barkhausen criteria for sustained oscillations of an oscillator.	1 M
9.	Draw the circuit diagram of non- inverting amplifier using op-amp.	1 M
10.	Define output offset voltage of an op-amp.	1 M
	PART-B Answer the following. Each question carries TEN Marks. 5x10=	50M
11	 A). i) Explain the operation of pn diode under forward and reverse biasing ii) Draw the circuit diagram of full wave rectifier and explain its operation with waveforms. 	5M 5M
	OR	
11.	 B). i) Draw the circuit diagram of a transistor in voltage divider bias and explain it with necessary equations. ii) An NPN transistor if β=50 is used in common emitter circuit with V_{CC}=10V and R_C=2KΩ. The bias is obtained by connecting 100KΩ resistor from collector to base. Find the quiescent point and stability factor. 	6M 4M
12.	A). With the help of neat sketch and characteristics curves explain the operation of the N-channel JFET.	10M
	OR	0.1
12.	 B). i) Draw the small signal equivalent circuit of CD amplifier. Derive the expressions for voltage gain, input and output impedances. ii) In the common source amplifier, consider R_D = 5KΩ, R_G=10MΩ, μ=50 and r_d=35KΩ.Calculate the voltage gain, input, and output impedances. 	6M 4M
13.	A). Draw the circuit diagram of dual input balanced output differential amplifier. Derive the expression for common mode and differential gain of the amplifier.	10M

13. B).	working. Also prove that its maximum efficiency is 50%.	TUIVI
14. A).	i) Draw the topology of current series feedback amplifier and what is the effect input and output impedances.	5M
	ii) Calculate the gain, input impedance and output impedance of voltage series feedback amplifier having A=300, R_i =1.5 $K\Omega$, R_o = 50 $K\Omega$ and β =1/20.	5M
	OR	
14. B).	i) Draw the circuit diagram of RC phase shift oscillator and explain its operation.	5M
	ii) Derive the expression for frequency of oscillations of a Wien bridge oscillator.	5M
15. A).	i) Define slew rate and derive the expression for it.	6M
ŕ	ii) Draw the circuit diagram of inverting amplifier and derive the expression for its closed loop gain.	4M
	OR	
15. B).	i) Explain the operation of square wave generator with circuit diagram.	5M
	ii) Find R ₁ and R _F in the integrator so that the peak gain is 20dB and the gain is 3dB down from its peak when $\alpha = 10000$ rad/sec. Use a capacitance of 0.01µF	5M \



(UGC AUTONOMOUS)

B.Tech II Semester Regular/Supplementary Examinations July/August-2024

Dat	(Electronics & Communication Engineering) te: 20.07.2024 FN Time: 3 hours	Max.Marks: (60
	(Note: Assume suitable data if necessary) PART-A Answer all TEN questions (Compulsory) Each question carries ONE mark.	10x1=10N	_
l. De	efine transition capacitance of a PN diode.	1	1 M
2. Ex	splain and draw piece wise linear characteristics of a PN diode.	1	1 M
8. W	hat is the maximum efficiency of a full wave rectifier without filter?	1	1 M
. De	efine Ripple factor in rectifier circuit.	1	1 M
. Bu	aild the relationship between α , β and γ.	_a 1	1 M
i. De	efine operating point of a load line.	. 1	1 M
. Ar	nalyze Why FET is called as a voltage control device.	1	1 M
. Li	st any two comparisons between P-channel and N-channel JFET in its construction	ı . 1	1 N
. Li	st some applications of Zener diode.	1	1 M
0. Dr	aw V-I characteristics of varactor diode.	1	1 M
	PART-B		
Ans	swer the following. Each question carries TEN Marks.	5x10=50	\mathbf{M}
1.A).	Draw and explain Forward and Reverse bias V-I characteristics of PN diode.	1	10N
	OR		
1. B).	i) Define and build the expression for static and dynamic resistances.ii) Draw the ideal diode characteristics.		5N 5N
2. A).	i) Explain the operation of two level Diode clipper circuit with neat circuit diagraw the transfer characteristics. ii) A sinusoidal voltage whose $V_m = 26$ volts applied to Half wave rectifier. The ideal and $R_L = 1.2 \mathrm{K}\Omega$. Find out peak value of load current, RMS value of load	Diode is	5N
	DC value of load current.		
2 D)	OR	u Danissa 1	1 (1)
2. B).	Draw and explain the circuit diagram of Half-wave rectifier with capacitor filter the Ripple factor and Efficiency equation.	er. Derive 1	10N
3. A).	i) Draw the circuit diagram of a transistor in CE configuration and explain the output characteristics with the help of different regions.ii) Derive the current relationship in Common Emitter configuration.	input and	6N
			4N
	OR		
3. B).	i) Explain the operation of Self bias Circuit and derive the expression for stability ii) The reverse leakage current of the transistor in CB configuration is $0.1\mu A$, v $16\mu A$ when the same transistor is connected in CE configuration. Calculate α , β and β	while it is	6N 4N

14. A).	i) Explain how MOSFET acts as capacitor.	5M
	ii) Explain the operation of P channel JFET with neat diagrams.	5M
	OR	
14. B).	Explain the constructional features of a N-channel depletion mode and Enhancement mode MOSFET and explain its basic operation with neat diagrams.	10M
15. A).	Explain the operation of UJT with neat diagram and draw its characteristics.	10M
	OR	
15. B).	Explain the operation of Tunnel diode with neat diagram and draw its characteristics.	10M



(UGC AUTONOMOUS)

B.Tech II Semester Regular/Supplementary Examinations July/August-2024

Course Name: Data Structures

(Common for CSE, CSC, CSM & CSD)

Date: 20.07.2024 FN

Time: 3 hours

Max.Marks: 60

(Note: Assume suitable data if necessary)

PART-A

Answer all TEN questions (Compulsory)

Each question carries ONE mark.

10x1=10M

1. Classify the different types of queues.

1 M

2. Evaluate the following "infix" expression is with the help of Stack:

1 M

5*(6+2)-12/4 What are the advantage and disadvantage of separate chaining and linear probing?

3.

5.

1 M

4. Define extendible hashing.

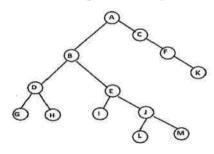
1 M

Discuss with respect to following tree:

1 M

a) List the siblings for node E.

b) Compute the height



6.	List out the various operations that can be performed on B-trees.	1 M
7.	Write the worst, average and best case time complexities of Quick sort.	1 M
8.	What is a graph and its types?	1 M
9.	What is tries?	1 M
10.	List Pattern Matching algorithms.	1 M

PART-B

Answer the following. Each question carries TEN Marks.

5x10=50M

11.A). Analyze and write a routine to check whether the queue is full or empty. For railway reservation the queue data structure is preferred –Justify.

OR

- 11. B). Write the applications and develop an algorithm to explain enqueue() and dequeue() 10M operations on queues.
- 12. A). i) Define Dictionary? Explain Skip-list representation of Dictionary data structure.

 5M
 ii) Develop an algorithm to explain Double Hashing.

OR

12. B). List the different types of hashing techniques? Explain Linear and Quadratic Probing 10M techniques in detail with an Example.

13. A). How does the AVL tree differ from binary search tree? Simulate the result of inserting 10M 3,1,4,6,2,8,9 into an initially empty AVL Tree. Analyze the properties of Red-Block Trees. Illustrate the steps in the construction of Red-10M 13. B). Block Trees with the following key values: 14, 54 12, 33, 67, 8, 7, 80, 5, 23, 52 Analyze the properties of heap, illustrate the steps in the construction of a heap with 10M following key values. 15,55,32,43,87,18,12,90,25,33,62 Explain with algorithm, How DFS be performed on a undirected graph. Show the 10M 14. B). algorithm for finding connected components of an undirected graph using DFS, and derive the time complexity of the algorithm. Explain Standard Tries, Compressed Tries and Suffix tries with example. 15. A). 10M **OR** 10M 15. B). Compare Brute force, Boyer -Moore algorithm and Knuth- Morris-Pratt algorithm.



B.Tech II Semester Regular/Supplementary Examinations July/August-2024

	Course Name: C Progra	amming and Data Structures	ř.	
	Dodge 22 07 2024 EDI	(Common for CE & ME)	χ.	
4	Date: 23.07.2024 FN		1ax.Marks: 60)
		(Note: Assume suitable data if necessary) PART-A		
		Answer all TEN questions (Compulsory)		
		Each question carries ONE mark.	10x1=10M	
1.	Define Program.	,	1 N	М
2.	Differentiate variable and o	constant.	1 N	
3.	Write down the syntax of c	ontinue statement.	1 N	
4.	Write a program to check v	vhether given number is even or odd.	1 N	
5.	Define array.		1 N	
6.	List any two predefined fur	nctions of strings.	1 N	
7.	Define data structure.		1 N	
8.	Mention the principle follow	wed in stack and queue.	1 N	
9.	Differentiate between searc		1 N	
10.	What is the underlying prin	ciple of insertion sort?	1 N	
		PART-B	1 1	,1
	Answer the following. Each	question carries TEN Marks.	5x10=50M	
11.A)	List the different types (examples.	of operators in C. Explain any four types of operators with	relevant 10N	M
		OR		
11. B). Explain any four c-toker	ns with examples.	10N	νſ
12. A	 Differentiate while and given number is palindre 	do-while using syntax. Write a program to check whe	ther the 10N	
		OR		
12. B)	 Explain the syntax of C arrays. 	One-Dimensional Array. Write a program to find the sum	of two 10M	Л
13. A)	 What are the string hand 	ling functions and explain any four?	10M	Л
		OR	1010	
13. B)	. Define pointer. Analyze	the concept of pointers with arrays using appropriate exam	ples. 10M	Л
14. A)	. What is single linked list	? Interpret the advantage of single linked list over arrays.	10M	
		OR .	1014.	1
14. B)	 What is Queue? Implement single linked list. 	ent the concept of Queue's insertion and deletion operation	us using 10M	1
15. A)	. Solve the following array 10 20 30 40 50 60	velements using the logic of binary search: 70 80	10M	1
		OR		
15. B).		thm to sort the below elements: 5 67 50	10M	ſ

H.T No:						R22	Course Code: A400101
1111 1101						1144	



	(Common for EEE, ECE & CSE) Date: 23.07.2024 FN Time: 3 hours	Max.Marks	s• 60
	(Note: Assume suitable data if necessary)	WIAX.WIAFKS	. 00
	PART-A		
	Answer all TEN questions (Compulsory) Each question carries ONE mark.	10x1=1	0M
1,.	Punctuate the given sentence.		1 M
	 I want to tell you about my dream Hasini told her best friend. 		
2.	Write <i>antonym</i> by using prefixes to the following word. • Proper		1 M
3.	Choose the appropriate homophones given in the brackets		1 M
	 Everyone walk down this please.(aisle/isle) 		
4.	Complete the sentences with suitable tense form of the given verb.		1 M
	 Your friends (wait) for you for an hour. 		
5.	Differentiate the following <i>confusing</i> words and use them in your sentences. • Principal - Principle		1 M
6.	Explain the following <i>foreign expression</i> and its usage:		1 M
	• Curriculum Vitae		
7.	Give the full form of SMS		1 M
F	Give the full form of Sivis		
8.	Eliminate the redundant word and rewrite the correct sentence.		1 M
	 Deepa got a free gift from her aunt. 		
9.	Choose the correct <i>pronoun</i> in the given sentence.		1 M
	 Let Mohan and (me/I) stay here 		
10	What is Intensive Reading?		1 M
	PART-B Answer the following. Each question carries TEN Marks.	5x10=5	50M
11	A). Explain the term "Bharat brand English" used by R.K. Narayan in 'Toasted E OR	nglish'.	10M
11	B). i) List out the essential features of a Good Paragraph.		5M
	ii) Write a paragraph on "Environmental Advantages of Solar Energy"		5N
12	A). What was Sudha Murthy's first experience of gender discrimination and her it?	reaction on	10M
	OR		
12	B). i) Define 'Reading Skill' and its benefits?		5M
	ii) Write a detail note on sub-skills of Reading: Skimming and Scanning.		5M
13	A). List out the four takeaways related to online learning that should be repandemic according to F. Haider Alvi.	tained post-	10M
		(P.T.O)	

- 13. B). Draft a cover letter and resume to the HR department of Amazon Company for the position of a software engineer with the qualification-- bachelor's/master's degree with the background in information systems, marketing and good Communication skills to work on company internet sites.
- 14. A). A.P.J.Abdul Kalam believed that 'students of art and literature are important contributors 10M in transforming India into a developed Nation'-- Discuss.

OR

- 14. B). What are the five steps of SQ3R techniques of reading? Why is it an effective method in Reading?
- 15. A). Your college has adopted a village as a Social Responsibility. Students are being taken to teach the children of that village on a regular basis. Draft a feasibility report for your college magazine on the various other programs organized by your college management in that village for its development.

OR

15. B). Correct and rewrite the following sentences:

10M.

- i) One must respect his parents.
- ii) The two friends must help one another.
- iii) Rohan and myself studied in the same school.
- iv) Each and every one have to finish their task.
- v) I, you and he will go to a movie tomorrow.
- vi) Neither he nor his friends is relieved.
- vii) The climate of India is better than Africa.
- viii) The African Countries are poor, isn't it?
- ix) The patient died before the doctor arrived.
- x) You should avail the offer.



(UGC AUTONOMOUS)

B.Tech II Semester Regular/Supplementary Examinations July/August-2024

Course Name: Basic Electrical Engineering

(Common for CSC, CSM & CSD)

	(Common for CSC, CSM & CSD)	
	Date: 23.07.2024 FN Time: 3 hours Max.Mark	s: 60
	(Note: Assume suitable data if necessary)	
	PART-A Answer all TEN questions (Compulsory)	
	Each question carries ONE mark. 10x1=1	.0M
1.	State Kirchoff's Voltage law.	1 M
2.	What are the applications of Thevenin's theorem?	1 M
3.	State the relationship between line voltage & phase voltage and line current & phase current of a 3phase delta connected system?	1 M
4.	What is a Resonant frequency?	1 M
5.	Write the emf equation of a transformer and define each term.	1 M
6.	Why are transformers rated in only kVA?	1 M
7.	What is an electric motor?	1 M
8.	Give the types of DC generator.	1 M
9.	What is the necessity of Electrical Earthing?	1 M
10.	Convert 10HP into watts.	1 M
	PART-B	
	Answer the following. Each question carries TEN Marks. 5x10=	50M
11.4	A). Derive the transient response of an RL circuit with DC excitation. OR	10M
11.	B). Two resistors R1 and R2 are connected in Parallel and a Voltage of 200V DC is applied to the terminals. The total current drawn is 20A, R1=30 Ω . Find R2 and power dissipated in each resistor.	10M
12.	A). Derive the relationship of line voltage & phase voltage and line current & phase current in 3-phase delta connected load.	10M
	OR	
12. 1	B). Derive Average and RMS value of Sinusoidal wave form.	10M
13.	A). Explain about Construction and working of auto transformer. OR	10M
13.]	3). Explain different types of 3-phase transformer connections with neat diagram.	10M
14.	A). Explain the Construction and working principle of DC motor with neat diagram? OR	10M
14.]		10M
15.	A). Explain the types of Wires and cables in detail. OR	10M
15. J	3). Explain Construction and working principle of MCCB with neat diagram.	10M



B.Tech II Semester Regular/Supplementary Examinations July/August-2024

Course Name: Building Materials, Construction and Planning

D	•	Engineering) ne: 3 hours Max	x.Marks: 60
4	(Note: Assume su	nitable data if necessary) PART-A questions (Compulsory)	
		carries ONE mark.	10x1=10M
1. V	What do you mean by quarrying?		1 M
2. I	Distinguish Natural and artificial seasoning.		1 M
3. I	Explain why gypsum is added during the man	ufacturing of cement.	1 M
i. Y	What is the soundness of cement?		1 M
5. V	What is a damp proof course?		1 M
5. I	Explain the different types of floors.		1 M
. I	Define pointing.		1 M
. I	Define workability of concrete.		1 M
. I	Illustrate two practical applications of scaffold	ling in construction.	1 M
0. \	What is floor area ratio (FAR)?		1 M
	I	PART-B	
$\frac{\mathbf{A}}{\mathbf{A}}$	answer the following. Each question carries	TEN Marks.	5x10=50M
1.A).	. i) Define the term wood and explain the re	inforced glass fibre bricks.	5M
	ii) Explain about characteristics of good by	_	5M
	, .	OR	
1. B)	. Write about the classification and quarrying	g methods.	10M
2. A)). i) List out and explain the chemical admix	tures.	5 M
Í	ii) Briefly explain about the hydration of c		5M
		OR	
2. B)	. List out the laboratory tests on cement and	explain Initial and final setting time tests.	. 10M
3. A)). i) Draw the plan and elevation of fully pan	el window.	5M
	ii) State briefly the requirement of good st	aircase	5M
		OR	
3. B)	. i) What do you mean by air conditioning?	Explain about any one method.	5M
	ii) Discuss about combined footings with r	neat sketches.	5M
4. A)	. i) Explain about properties and advantages	of Aluminum composite panel.	5M
	ii) Define shoring and explain about any o	ne method of shoring.	5M
		OR	
4. B)	. i) List out types of bonds in brick masonry	and explain any bond with a neat sketch.	5M
	ii) Explain underpinning and discuss about	t its uses.	5M
		(P.	T.O)

15. A).	i) Explain briefly the practical considerations in building planning.	5M
	ii) Explain the classification of buildings with material specifications.	5M
	OR	
15. B).	i) Explain the Building Bye-laws.	5M
	ii) What are the classifications of building based on type of construction?	5M

H.T No: **R22** Course Code: A403301



CMR COLLEGE OF ENGINEERING & TECHNOLOGY

	(UGC AUTONOMO)	S & TECHNOLOGY (S)
	D. I ech II Semester Regular/Supplementary Fy	aminations July/August-2024
	Course Name: Engineering Materials (Mechanical Engineer	
	Date: 25.07.2024 FN Time: 3 hours	
	(Note: Assume suitable data if	Max.Marks: 60
	PART-A	
	Answer all TEN questions (Co Each question carries ONE)	2000 (Editor)
1.		nark. 10x1=10M
2.	Differentiate elastic and plastic deformation.	1 N
3.	List various Mechanical properties of metal.	1 N
4.	Classify steel based on Carbon contest.	1 N
5.	Mention any two industrial applications of Nickel.	1 N
6.	Classify composite materials.	1 M
7.	Write differences between hand layup and spay layup.	1 M
8.	List important sources of plastics.	1 M
9.	What are the applications of ceramics?	1 M
9. 10.	What are the function requirements of nanoparticles?	1 M
10.	Give examples of any two biomaterials.	1 M
A	Answer the following Fook and it	1 171
	Answer the following. Each question carries TEN Marks.	5x10=50M
11.A)	on plant stress strain diagram for ductile at	nd brittle materials. State few
		10M
11. B)	OR	
11. 0)	i) Significance of Ashby's chart.ii) Discuss any three ASTM standards for testing.	4M
		CM.
12. A)). Write composition properties and applications of grey cast	iron and white cost iron
	OR	
12. B).	monitorious anoys. Discuss any two nonforme	ous allows with some "
	properties and applications.	10M
13. A).	Define composites. Discuss the functional requirements composite materials.	5
	composite materials.	of matrix and significance in 10M
	OR	
13. B).	. Discuss the characteristics of composite materials in detail.	
14. A).		10M
,	. Explain the processing methods of Polymers and application	s. 10M
14. B).	OR Explain any two coronic files of	
,	any two columne labrication techniques.	10M
15. A).	Discuss the characteristics and potential applications of meta	l nonomout' 1
	OR	
15. B).	Explain the significance of semiconductor Nanomaterials as	Compared with bull- c
	****	ompared with bulk form. 10M